SILICON EPITAXIAL PLANAR SCHOTTKY BARRIER DIODE

Features

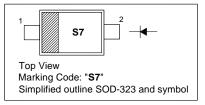
- Small surface mounting type
- High reliability

Applications

• Low current rectification

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V_{RM}	45	V
Reverse Voltage	V _R	40	V
Mean Rectifying Current	Io	0.1	А
Peak Forward Surge Current (60 Hz for 1 Cyc.)	I _{FSM}	1	А
Junction Temperature	T _j	125	°C
Storage Temperature Range	T _s	- 40 to + 125	°C

Characteristics at T_a = 25 °C

Parameter	Symbol	Тур.	Max.	Unit
Forward Voltage at $I_F = 100 \text{ mA}$ at $I_F = 10 \text{ mA}$	V _F V _F		0.55 0.34	V V
Reverse Current at V _R = 10 V	I _R	-	30	μΑ
Capacitance Between Terminals at $V_R = 10 \text{ V}$, $f = 1 \text{ MHz}$	Ст	6	-	pF

Note: ESD sensitive product handling required.









SEMTECH ELECTRONICS LTD. (Subsidiary of Sino-Tech International Holdings Limited, a company listed on the Hong Kong Stock Exchange, Stock Code: 724)

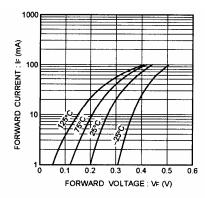


Fig. 1 Forward characteristics

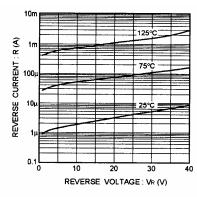


Fig. 2 Reverse characteristics

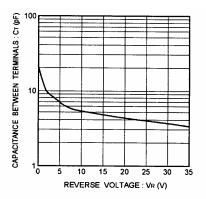


Fig. 3 Capacitance between terminals characteristics

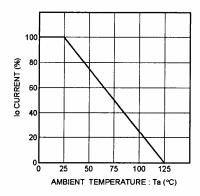


Fig. 4 Derating curve (mounting on glass epoxy PCBs)









ISO/TS 16949 : 2002 ISO 14001:2004 ISO 9001:2000 Certificate No. 05103 Certificate No. 7116 Certificate No. 0506098

PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-323

